

## **IN THE SPECIFICATION**

*Please insert the following paragraph on page 1 after the title of the invention and before the "Technical Field":*

--Related Application

This application is a national phase of PCT/JP2005/002874 filed on February 23, 2005, which claims priority from Japanese Application No. 2004-053842 filed on February 27, 2004, the disclosures of which Applications are incorporated by reference herein. The benefit of the filing and priority dates of the International and Japanese Applications is respectfully requested.--

*The following paragraphs will replace all prior versions of themselves in the specification of the application.*

1) Please amend the paragraph [0060] as follows:

[0060] Figure 8 is a graph plotting the targeted values and the measured values of the internal pressure of the pipe and the flow rates of the buffering gas with regard to the heating positions in Example 1. In Example 1, the amount of the gas 1 introduced from the first buffering gas inlet portion was changed from 2 to 18 SLM by pattern control. In addition, the amount of the gas 2 introduced from the second buffering gas inlet portion was changed from 10 to 20 SLM by feedback control according to differences between the measured value and the targeted value of the internal pressure of the silica glass pipe. As a result, a difference between the internal pressure of the silica glass pipe and the targeted value could be

suppressed to a very small value of  $\pm 3$  Pa, and satisfactory control could be achieved.

2) Please amend the paragraph [0061] as follows:

[0061] In Example 2, using the apparatus 201 for producing an optical fiber preform, the amount of the buffering gas 1 introduced was pattern-controlled by the first control means according to heating positions, and the amount of the buffering 2 gas introduced was feedback-controlled by the second control means so that the internal pressure of the pipe might be a targeted value. Figure 9 is a graph plotting the targeted values and the measured values of the internal pressure of the pipe and the flow rates of the buffering gas with regard to the heating positions in Example 2. The silica glass pipe and heat source used were the same as in Example 1. A preform was produced under conditions in which a heat source velocity was 150 mm/min, the highest temperature of the outer surface of the silica glass pipe was 2200°C, the deposition rate of a glass layer was 1 g/min, and a targeted refractive index difference of the glass layer relative to pure silica glass was 0.40%. The amount of exhaust was controlled so that the internal pressure of the silica glass pipe might be about -30 Pa without a flow of a buffering gas. Under these conditions, ten glass layers were deposited by the MCVD method.

3) Please amend the paragraph [0075] as follows:

[0075] Therefore, when the rate of change in the internal pressure of the pipe ~~per unit time~~ is limited to  $\pm 50$  Pa/sec or less, more preferably  $\pm 30$  Pa/sec or less, fluctuation in the outer diameter can be suppressed, and a satisfactory MCVD method can be carried out. When the rate of change in the internal pressure is limited, a rate of change of  $\pm 10$  Pa/sec or more may be allowed.